

Silicon NPN Darlington Power Transistors

2SD2439

DESCRIPTION

- With TO-3PML package
- Complement to type 2SB1588

APPLICATIONS

- Audio ,series regulator and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

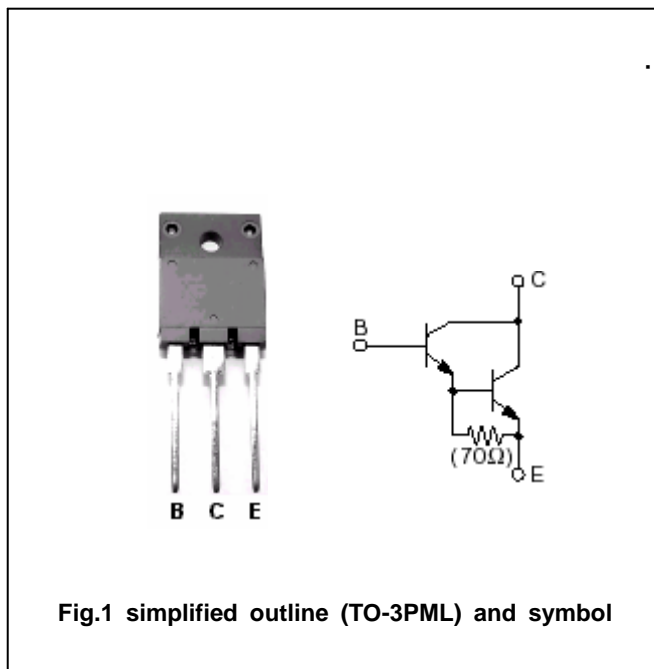


Fig.1 simplified outline (TO-3PML) and symbol

Absolute maximum ratings(Tc=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	160	V
V _{CEO}	Collector-emitter voltage	Open base	150	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		10	A
I _B	Base current		1	A
P _C	Collector power dissipation	T _C =25	80	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50mA; I_B=0$	150			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=7A; I_B=7mA$			2.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=7A; I_B=7mA$			3.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=160V; I_E=0$			100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V; I_C=0$			100	μA
h_{FE}	DC current gain	$I_C=7A; V_{CE}=4V$	5000			
f_T	Transition frequency	$I_C=2A; V_{CE}=12V$		55		MHz
C_{OB}	Output capacitance	$I_E=0; V_{CB}=10V; f=1MHz$		95		pF

Switching times

t_{on}	Turn-on time	$I_C=7A; R_L=10\Omega$ $I_{B1}=-I_{B2}=7mA$ $V_{CC}=70V$		0.5		μs
t_s	Storage time			10.0		μs
t_f	Fall time			1.1		μs

◆ **h_{FE} classifications**

O	P	Y
5000-12000	6500-20000	15000-30000

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PACKAGE OUTLINE

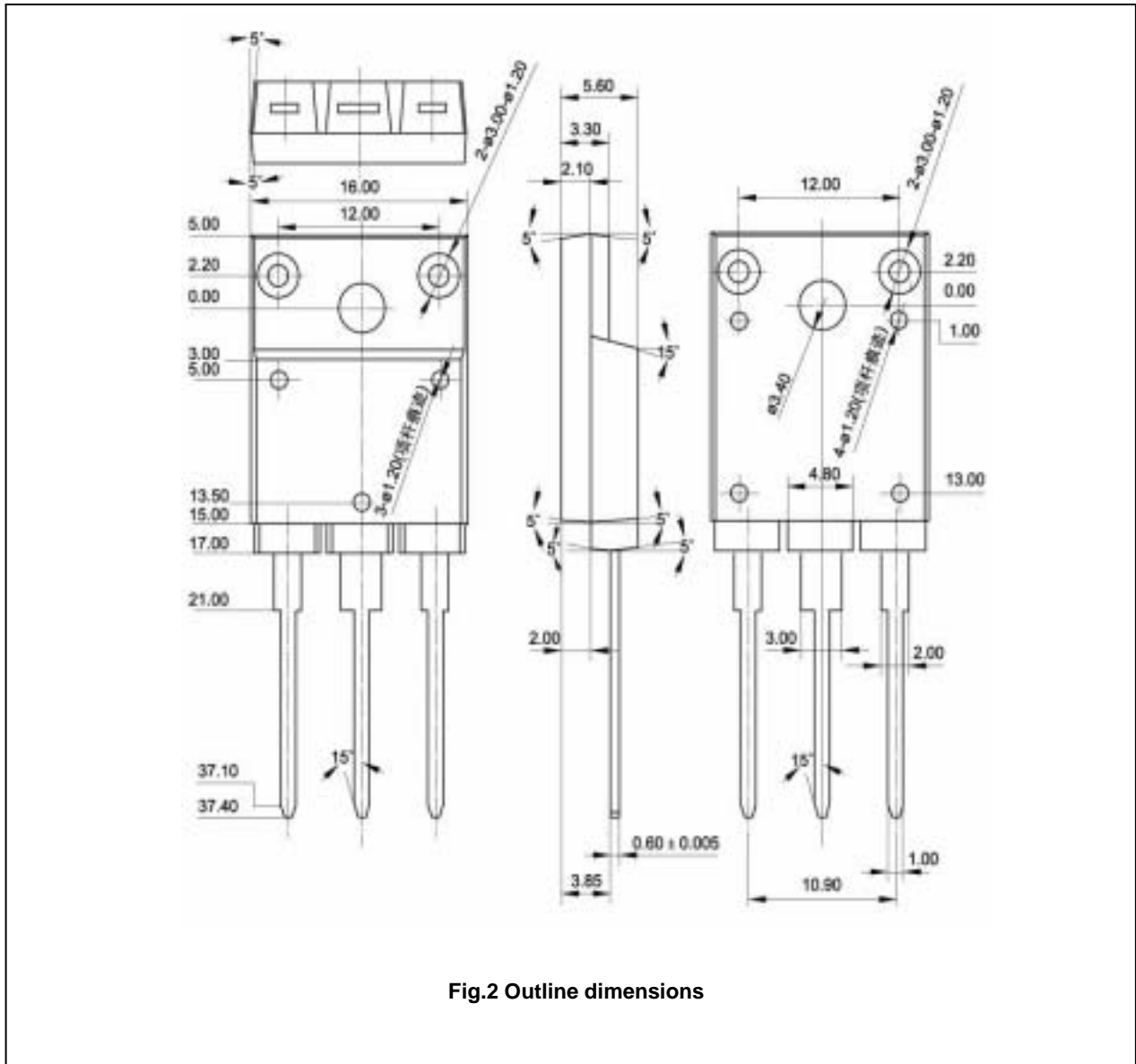


Fig.2 Outline dimensions